

Product Overview

NGTB20N135IHR: IGBT 1350V 20A FS2-RC Induction Heating

For complete documentation, see the data sheet.



This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS)Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications.

Features

- Optimized for Low Case Temperature in IH Cooker Applications
- Extremely Efficient Trench with Fieldstop Technology
- 1350V Breakdown Voltage
- Reliable and Cost Effective Single Die Solution

Benefits

- Low Switching Loss Reduces System Power Dissipation

Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{CE(sa)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit With stand (μ s)	E_{AS} Typ (mJ)	P_D Max (W)	Co- Pack aged Diode	Pack age Type
NGTB20N135IHRWG	Pb-free Halide free	Active	1350	20	2.2	1.8	0.6	-	-	-	234	-	-	394	Yes	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

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